

^{46}V IT decay 1982Si15,1967Co12,1962Mo19

Type	Author	History Citation	Literature Cutoff Date
Full Evaluation	S. -c. Wu	NDS 91, 1 (2000)	15-Jul-2000

Parent: ^{46}V : E=801.1 10; $J^\pi=3^+$; $T_{1/2}=1.02$ ms 7; %IT decay=100.0

Produced in $^{32}\text{S}(^{16}\text{O},\text{pn})$ E=50 MeV (1982Si15); pulsed beam, 2 NaI detectors; measured perturbed $\gamma(\theta)$ in magnetic field.

Produced in $^{46}\text{Ti}(\text{p},\text{n})$ E=17.5 MeV (1967Co12), pulsed beam, Ge(Li) detector; E=19.2 MeV, (1962Mo19), pulsed beam, NaI detector; measured $T_{1/2}$.

 ^{46}V Levels

E(level)	J^π †	$T_{1/2}$	Comments
0.0	0^+		
801.1 10	3^+	1.02 ms 7	J^π : from E(level), $T_{1/2}$, and $\gamma(\theta)$ one gets $J=3$. g=+0.546 10 from analysis of perturbed $\gamma(\theta)$ (1982Si15). $T_{1/2}$: weighted average of 1.04 ms 10 (1967Co12) and 1.0 ms 1 (1962Mo19) from decay of 801 γ .

† From Adopted Levels.

 $\gamma(^{46}\text{V})$

E_γ	I_γ †	$E_i(\text{level})$	J_i^π	E_f	J_f^π	Mult.	Comments
801.1 10	100	801.1	3^+	0.0	0^+	[M3]	E_γ : from 1967Co12.

† Absolute intensity per 100 decays.

 ^{46}V IT decay 1982Si15,1967Co12,1962Mo19Decay Scheme

Intensities: $I_{(\gamma+ce)}$ per 100 parent decays
%IT=100.0

